

# Thermal melting of a quantum electron solid in the presence of strong disorder: Anderson versus Wigner

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We consider temperature-induced melting of a Wigner solid in a one dimensional (1D) chain of electrons interacting via the long-range Coulomb interaction in the presence of strong disorder arising from charged impurities in the system. The system is the 1D analog of many semiconductor-based 2D electron layers where Wigner crystallization is often claimed to be observed experimentally. Using exact diagonalization and utilizing the inverse participation ratio to distinguish between the localized insulating solid phase and the extended metallic liquid phase, we find that the effective melting temperature may be strongly enhanced by disorder since the disordered crystal typically could be in a localized glassy state incorporating the combined nonperturbative physics of both Anderson localization and Wigner crystallization. This disorder-induced enhancement of the melting temperature may explain why experiments often manage to observe insulating disorder-pinned Wigner solids in spite of the experimental temperature being decisively far above the theoretical melting temperature of the pristine Wigner crystal phase.

*Introduction and background* - Wigner predicted more than 80 years ago that an interacting electron liquid would crystallize at  $T = 0$  into a quantum solid at a sufficiently low density, below some dimension-dependent critical density, because of their long range Coulomb interaction [1]. The basic idea is simple: the quantum non-interacting kinetic energy (i.e. “quantum fluctuations”) for an electron density of  $n$  in a  $d$ -dimensional system typically goes as  $n^{-2/d}$  simply by virtue of the uncertainty principle whereas the Coulomb interaction potential energy ( $\sim 1/\text{distance}$ ) goes as  $n^{-1/d}$ , implying that for low enough  $n$ , the system would minimize the potential energy by crystalizing into a solid phase instead of being a liquid (as happens at higher densities) which minimizes the kinetic energy. In contrast to a classical system, which is always a solid at  $T = 0$  because there is no classical kinetic energy at zero temperature, a quantum Wigner solid would melt into a quantum electron liquid even at  $T = 0$  by virtue of quantum fluctuations. Typically, the critical density separating the Wigner solid and the electron liquid phase is very low, and observing a density-tuned quantum Wigner solid is a huge experimental challenge. On the other hand, if the temperature is high enough ( $T > T_F$ , where  $T_F$  is the non-interacting Fermi temperature), then it is in principle possible for the electrons to undergo a liquid-to-solid transition with increasing density (in contrast to the quantum crystallization, happening with decreasing density) at a finite temperature. Such a classical liquid to solid transition was indeed observed in two-dimensional (2D) electrons on the surface of liquid helium a long time ago [2, 3]

The current work focuses on the thermal melting of the quantum Wigner solid in the presence of disorder. The density- temperature mean field phase diagram of the disorder-free pristine electron solid to liquid transition has been calculated in earlier works [4, 5]. In 2D systems, the solid-to-liquid density-tuned  $T = 0$  quantum

transition occurs at  $r_s = r_c \sim 40$ , where  $r_s$  is the usual dimensionless average electron separation measured in the units of effective Bohr radius ( $r_s$  is also the effective dimensionless Coulomb coupling parameter, being the ratio of the average Coulomb energy to the Fermi energy—large  $r_s$  implies low density and strong effective Coulomb interaction). For  $r_s = r_c$ , the melting temperature of the Wigner solid is  $T_m = 0$ , and  $T_m$  increases with increasing  $r_s$ , eventually at large enough  $r_s$ , at a given  $T$ , the system enters the classical regime where  $T > T_F$ . In Ref. [4], where the  $T - n$  phase diagram for the 2D electron solid-liquid transition was obtained by interpolating between the classical [6] and the quantum [7] theories, the highest melting temperature for the Wigner solid was determined to be  $\sim 10$  mK for GaAs which happens for  $r_s \sim 60 \sim 1.5r_c$ . For other semiconductors,  $T_m$  scales approximately as  $\sim m/\kappa^2$ , where  $m, \kappa$  are the effective mass and the background dielectric constant, respectively. This implies that the maximum possible  $T_m$ , occurring at the extreme low carrier density of  $r_s \sim 60$ , in 2D semiconductor materials is 1-50 mK, and should be virtually unobservable (since typically  $r_s \sim 60$  is not achieved in these 2D systems, implying a  $T_m$  much smaller than the maximum allowed  $T_m$ ).

It is therefore extremely puzzling that there are many experimental claims of the observation of 2D quantum Wigner crystallization based on transport measurements in 2D electron (or hole) gases confined in semiconductor layers, typically carried out around  $r_s \sim 25 - 40$ , where the theoretically predicted  $T_m$  is much smaller than the experimental base temperature of 20 mK in the dilution fridge [8–11]. Given how low the calculated melting temperature of the quantum Wigner crystal appears to be, even at extreme low carrier densities of  $r_s \sim 40$ , it seems unlikely that any existing experiment is capable of observing the pristine Wigner crystallization typically predicted by first principles  $T = 0$  QMC calculations [7, 12].

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In the current work, we propose and validate by exact small system numerical calculations that the correct interpretation of these experimental observations lies in including disorder effects in the theory—in particular, disorder in some sense enhances the effective melting temperature of the localized solid insulating phase compared with the extremely low melting temperature of the pristine system. Since the disorder in the high quality semiconductor layers arises invariably from random charged impurities which also interact with the electrons via the same long range Coulomb coupling as the electron-electron mutual interaction itself is, it is imperative to include both electron-impurity and electron-electron interactions on an equal footing. In fact, the  $r_s$  value of 40 ( $\sim r_c$ ) in 2D GaAs electron layers corresponds to a 2D carrier density of  $< 10^9 \text{cm}^{-2}$ , which is likely to be comparable to the random charged impurity density even in the highest quality semiconductor structures [13, 14], thus reinforcing the necessity of treating both electron-electron and electron-impurity interactions on an equal nonperturbative footing.

*Model and theory* - In order to calculate the transport properties of an interacting electron system nonperturbatively in the presence of quenched charged impurities, we use the exact diagonalization technique to solve the problem for a small finite system without any approximation. But such an exact diagonalization approach is not computationally feasible in a 2D interacting system in a meaningful manner, so we carry out our calculations in a 1D disordered electron system at finite temperatures. Since our interest is the thermal melting of the electron solid phase, particularly investigating how disorder affects the melting temperature, the 1D calculation should provide a good qualitative description for what happens also in 2D because the pristine Wigner solid to quantum liquid density-temperature phase diagrams are essentially identical qualitatively in 1D and 2D as can be seen by comparing Fig. 8 in Ref. [5] for the 1D phase diagram with Fig. 4 in Ref. [4] for the 2D phase diagram. Since the 1D finite size exact calculation is feasible, and the 2D is not, our work applies quantitatively to the 1D system and qualitatively to the 2D system. What we address is not so much the absolute quantitative phase diagram, but how increasing disorder affects the transport properties at finite temperatures, particularly whether localization persists to higher temperatures in the solid phase with increasing disorder.

Our model is minimal: A finite 1D chain of  $N_s = 16$  lattice sites with  $N_e = 4$  interacting spinless fermions with a hopping energy  $t = 1/a^2$ , where  $a$  is the lattice constant and with periodic boundary conditions. The use of spinless fermions is only for computational convenience, and affects no aspect of the key issues we address as we are not interested in the difficult energetic question of whether the solid phase is ferromagnetic or not (which necessitates a calculation of very small exchange

energies to better than  $10^{-6}$  precision). The interacting Hamiltonian is given by

$$H = \sum_i t(c_i^\dagger c_{i+1} + c_{i+1}^\dagger c_i) + V_i n_i + \sum_{i < j} U_{i,j} n_i n_j. \quad (1)$$

with the interaction  $U$  being the long-range Coulomb coupling

$$U_{i,j} = \left[ \frac{aN_s}{\pi} \left| \sin \frac{\pi(i-j)}{N_s} \right| \right]^{-1} \quad (2)$$

and the impurity-induced potential  $V$  being

$$V_i = -\frac{V}{a} \sum_j \left[ \frac{N_s}{\pi} \left| \sin \frac{\pi(i-X_j)}{N_s} \right| + \delta \right]^{-1} \quad (3)$$

with  $\delta = 1$  is the short-range regularization and  $X_j$  is the position of the impurity (note that the impurity potential is long-ranged consistent with the known disorder in semiconductor materials arising from quenched charged impurities [13, 14]). We diagonalize the Hamiltonian exactly to obtain all the interacting eigenstates, and then introduce the system temperature  $T$  by obtaining the finite-temperature occupancies through the usual canonical thermal distribution  $\langle n_i \rangle_T = \sum_j \langle \psi_j | n_i | \psi_j \rangle e^{-E_j/T} / \mathcal{Z}$  with  $\mathcal{Z}$  being the partition function. Using the exact  $\langle n_i \rangle_T$ , we calculate the key operational quantity defining transport, namely, the inverse participation ratio, IPR, defined by:

$$\text{IPR} = \left[ \frac{N_s}{N_e^2} \sum_i \langle n_i \rangle_T^2 \right] \left( \frac{N_s}{N_e} - 1 \right)^{-1}. \quad (4)$$

It is well-known that a localized insulating (extended metallic) system has  $\text{IPR} = 1$  (0) in the thermodynamic limit, and the IPR is used extensively in studying electronic transport properties both for interacting and for noninteracting systems. There is, however, a serious problem in finite systems, where the IPR is always finite and  $< 1$  simply because even localized states can never have strictly zero conductance in finite systems. Typically small (large) IPR values are associated with metallic (insulating) states, and we make the arbitrary distinction that  $\text{IPR} > (<) 0.4$  denotes the insulating solid (metallic liquid) phase. This is the quantum melting analog of the extensively used Lindemann criterion in classical statistical mechanics where melting is arbitrarily defined by the thermal mean square fluctuations of the solid phase around individual equilibrium sites being larger than some predefined amount in units of interparticle separation. We emphasize that the critical IPR-value (e.g. 0.4) has no effect on our qualitative thermal phase diagram, as we have explicitly verified by changing the critical IPR between 0.3 – 0.6 which produces identical-looking phase diagrams as presented in the next section of this paper. One cautionary note in order to

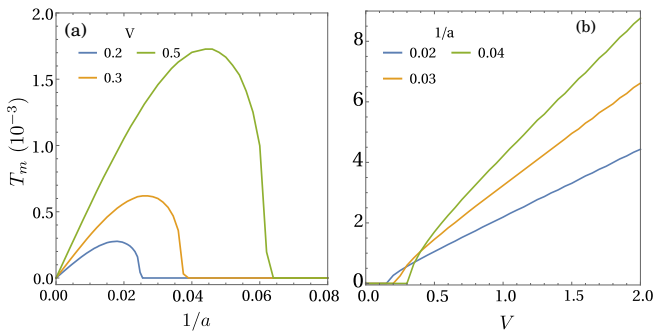


FIG. 1. Melting temperature  $T_m$  separating the non-interacting ( $U = 0$ ) conducting and insulating phases with respect to the carrier density  $1/a$  (a) and disordered strength  $V$  (b).

avoid any confusion is that the hopping kinetic energy  $1/a^2$  in our lattice model is equivalent to the Fermi energy or density in the standard continuum electron gas model (as applies to the semiconductor-based experimental systems), so we should loosely think of the lattice spacing  $a$  in our lattice model as qualitatively equivalent to  $r_s$  in the electron gas model. Even though our numerical simulations keep the number of electrons and sites fixed, the varying of  $1/a$  can be thought of as tuning the carrier density in experiments.

*Results and discussion* - For a perspective, we first provide the calculated  $T - V$  and  $T - a$  phase diagrams in Fig. 1 for the noninteracting system with  $U = 0$ . As expected, Anderson localization prevails and the melting temperature  $T_m$  increases monotonically with increasing  $V$ , and  $T_m$  is small only for very strong hopping and very weak impurity potential (by virtue of our system being finite).  $T_m$  here distinguishes the metallic conducting phase ( $T > T_m$ ) and the insulating localized phase ( $T < T_m$ ).

Figure 2 presents our key results for the interacting disordered system as a function of the kinetic energy (Figs. 2a and b) and the disorder strength (Fig. 2c). The physics of the interplay among temperature, disorder, kinetic energy (i.e. carrier density in the electron gas model) and interaction is manifestly obvious in Fig. 2 (particularly when compared with Fig. 1). For weak disorder,  $V < 4$ , Fig. 2a, the phase diagram is qualitatively the same as the pristine Wigner solid phase diagrams presented in Refs. [4, 5], once we take into account the fact that our kinetic hopping energy  $1/a^2$  on the lattice is equivalent to the Fermi energy (or the carrier density) in the electron gas which increases with carrier density (i.e.  $a \sim r_s$ ). Basically  $T_m$  is nonmonotonic, vanishing for large and zero kinetic energy and manifesting a maxima close to the vanishing of  $T_m$  at large kinetic energy equivalent to the critical  $r_c$  (at  $T = 0$ ) for the Wigner transition of the QMC calculations [7, 12]. We point out the interesting nonmonotonicity (as a function of  $V$ ) ap-

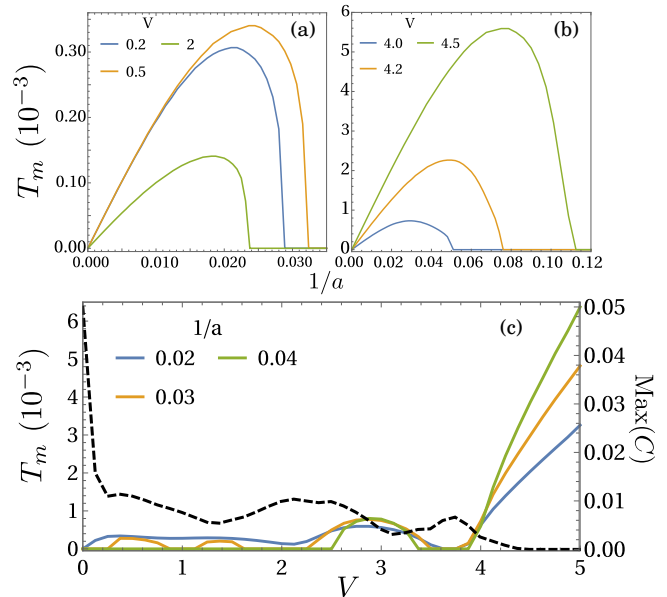


FIG. 2. (a-b) Melting temperature with respect to  $1/a$  in the Wigner crystal ( $V < 4$ ) (a) and Anderson insulator phase ( $V > 4$ ) (b). (c) Melting temperature with respect to  $V$ . The black dashed line represents the maximum value of density correlation for  $1/a = 0.03$  at the melting temperature.

parent in Fig. 2a in the weak disorder regime ( $V < 4$ ) as compared to the strong disorder regime ( $V > 4$ ) in Fig. 2b.

The most important and interesting result for our purpose is, however, Fig. 2c showing  $T_m$  as a function of disorder strength, and a manifest Wigner-to-Anderson ‘transition’ happens at  $V = 4$  where  $T_m$  increases monotonically with  $V$ , indicating that the insulating phase is stabilized by increasing disorder in contrast to the behavior for  $V < 4$  where the system is essentially a Wigner solid with small  $T_m$  as found in [4, 5]. Rather amazingly, this Wigner-to-Anderson transition in Fig. 2c looks essentially like a sharp transition at a critical  $V$  ( $\sim 4$ ) almost independent of carrier density  $1/a$  except that  $T_m$  in the Anderson-localized phase is progressively lower for smaller carrier density for  $V > 4$ . We also compute the density-density correlation  $C(j - i) = \langle n_i n_j \rangle_T - \langle n_i \rangle_T \langle n_j \rangle_T$ , which can only take positive values in the strongly interacting Wigner crystal phase [5]. The maximum value  $\text{Max}(C)$  at the melting temperature shown in Fig. 2c displays a visible drop at  $V = 4$ , indicating that the localized phase is indeed Wigner (Anderson) for  $V < (>)4$ . We believe that Fig. 2c provides the explanation for why the low-density 2D electron systems manifest strongly insulating solid-like behavior at temperatures far above the putative melting temperature of the pristine Wigner crystal. It is simply because the realistic solid phase is essentially an Anderson insulator with a large  $T_m$  (even for our small system size).

To show the generality of our finding, we present the same results as in Fig. 2, but now for two impurities of equal strength  $V$  placed at  $X_j = 1, 9$  in Figs. 3(a-b) and for impurities present at all sites but having a quasirandom strength  $\propto \cos(2\pi j/\beta)$  with  $\beta = (\sqrt{5} + 1)/2$  mimicking the randomness in Figs. 3(c-d). While the  $T - a$  phase diagrams are identical qualitatively to the single impurity results, the critical  $V$  for the crossover to Anderson localization is significantly reduced. As shown in Fig. 3(b), even though the impurity density only increases two fold, the critical  $V$  characterized by the sharp drop in the density correlation decreases 8-fold to  $\sim 0.5$  from  $\sim 4$ . This shows that if the impurity density is comparable to the carrier density, the localized phase is most likely an Anderson insulator.

We have also calculated density patterns and the density correlations in the various finite-temperature phases ensuring that indeed the three phases, metallic liquid ( $T > T_m$ ) and the Wigner solid and the Anderson insulator, manifest the expected behavior well-known for these phases: metallic liquid exhibiting uniform density throughout, the Wigner solid phase showing the periodic density modulation, and the Anderson insulator exhibiting a density localized at the impurities. We have also carried out calculations for the corresponding repulsive impurity potential, and the results corresponding to Figs. 1,2,3 remain the same with the only difference being that the electron density in the Anderson insulator phase now localizes away from the impurity. All our results remain qualitatively the same independent of the critical IPR used to define  $T_m$  in the phase diagrams.

*Conclusion* - We consider using the exact diagonalization technique the thermal melting of a disordered interacting Wigner solid, finding that increasing disorder causes a sharp crossover from the Wigner solid phase to a disorder-induced Anderson insulator phase with a concomitant huge increase in the melting temperature with increasing disorder (with the Wigner crystal phase itself being slightly suppressed by disorder with a decrease in the melting temperature). A direct qualitative implication of our theory is that the experimentally observed low-density insulating phase invariably observed in all 2D semiconductor systems is invariably exploring the Anderson insulator modulated by interaction effects even at the very low carrier densities below the putative critical density for the pristine electron liquid to Wigner solid phase because the 2D semiconductor invariably has Coulomb disorder in its environment as reflected in the finite mobility in the liquid phase. The typical maximum melting temperature of the pristine Wigner solid phase is extremely low ( $\sim 10$  mK), but disorder enhances this melting temperature substantially creating a crossover Anderson-Wigner glassy phase with high melting temperature as shown in the current work. Interestingly, the crossover from the Wigner to Anderson solid is abrupt at a threshold (non-universal) value of the disorder strength.

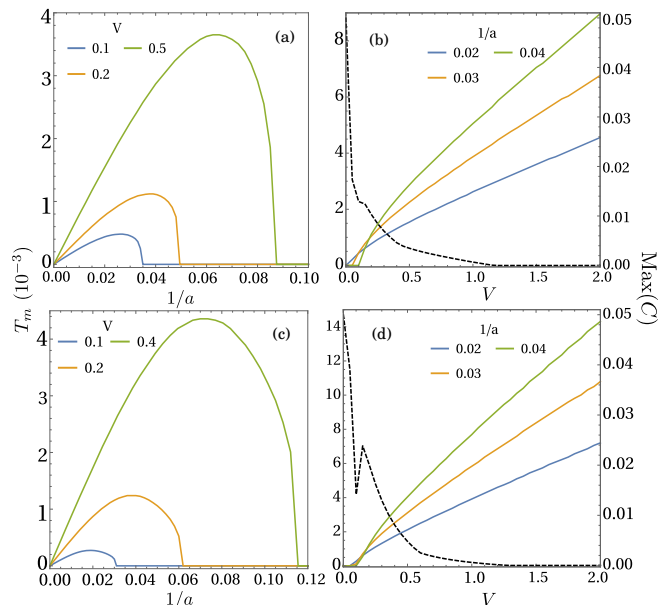


FIG. 3. Same as Fig. 2 but for the lattice having two equal impurities (a-b) and quasirandom-strength impurities at all sites (c-d). The black dashed lines are the maximum value of density-density correlation for  $1/a = 0.03$  at the melting temperature for each case.

The fact that disorder must always dominate the low-density phase is easily seen from a simple scaling argument involving the energetics of kinetic energy, Coulomb interaction energy, and the Coulomb disorder, which scale respectively as  $n$ ,  $n^{1/2}$ , and  $n^{-1}$  as a function of carrier density  $n$ . Thus, while it is indeed true that in the pristine system with no disorder, eventually the Coulomb interaction dominates the kinetic energy at low enough  $n$ , leading to Wigner crystallization at low density in the pristine system, the behavior of the disordered interacting system is fundamentally different from the pristine system since Coulomb disorder becomes by far the most dominant effect (going as  $1/n$ ) at low enough density. This means, no matter what, the system is asymptotically always an Anderson insulator at low enough density as long as there is any disorder! Our exact results explicitly verify this qualitative dominance of Anderson over Wigner at low densities. We note that the same remains true, although in a quantitatively weaker manner, for strongly screened Coulomb disorder or even strict short-range disorder since the energy scale of such a short-range disorder is  $\sim n^0$  (i.e. independent of density), which would eventually dominate the kinetic energy ( $\sim n$ ) and the Coulomb interaction energy ( $\sim n^{1/2}$ ) at low enough density. Thus the eventual dominance of Anderson over Wigner is guaranteed in all electronic materials studied in the laboratory, and therefore, an insulating Anderson localized phase is always the ultimate low-density phase of all metals. An equivalent physical way of saying the same thing is that a given sam-

ple has a fixed impurity density  $n_i$ , and for low enough carrier density  $n$ , disorder must always eventually win over interaction.

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